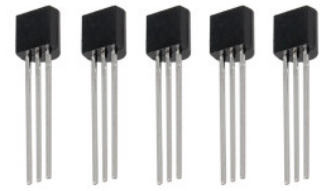




PRODUCT NAME : PN3565 NPN General Purpose Transistor (Pack of 5)

PRICE : Rs 20.00

SKU : RM2017



SEE THE PRODUCT PAGE FOR COMPLETE DATA SHEET Copyrights by Robomart.com

DESCRIPTION

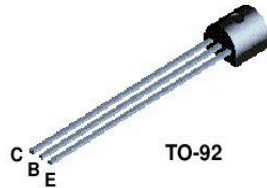
Features

- Collector-Emitter Volt (V_{ce0}): 25V
- Collector-Base Volt (V_{cb0}): 30V
- Collector Current (I_c): 500mA
- h_{fe} : 2-12 @ 1mA
- Power Dissipation (P_{tot}): 625mW
- Type: NPN



*Discrete POWER & Signal
Technologies*

PN3565



NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	25	V
V _{CBO}	Collector-Base Voltage	30	V
V _{EB0}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		PN3565	
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	°C/W

NPN General Purpose Amplifier
 (continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 2.0\text{ mA}, I_B = 0$	25		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\text{ }\mu\text{A}, I_E = 0$	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\text{ }\mu\text{A}, I_C = 0$	6.0		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 25\text{ V}, I_E = 0$		50	nA

ON CHARACTERISTICS*

h_{FE}	DC Current Gain	$V_{CE} = 10\text{ V}, I_C = 1.0\text{ mA}$	150	600	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1.0\text{ mA}, I_B = 0.1\text{ mA}$		0.35	V

SMALL SIGNAL CHARACTERISTICS

C_{ob}	Output Capacitance	$V_{CB} = 5.0\text{ V}$		4.0	pF
h_{ie}	Input Impedance	$I_C = 1.0\text{ mA}, V_{CE} = 5.0\text{ V},$ $f = 1.0\text{ kHz}$	2.0	20	k Ω
h_{oe}	Output Admittance	$I_C = 1.0\text{ mA}, V_{CE} = 5.0\text{ V},$ $f = 1.0\text{ kHz}$	0.5	35	μmhos
h_{fe}	Small-Signal Current Gain	$I_C = 1.0\text{ mA}, V_{CE} = 5.0\text{ V},$ $f = 20\text{ MHz}$ $I_C = 1.0\text{ mA}, V_{CE} = 5.0\text{ V},$ $f = 1.0\text{ kHz}$	2.0 120	12 750	

*Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

